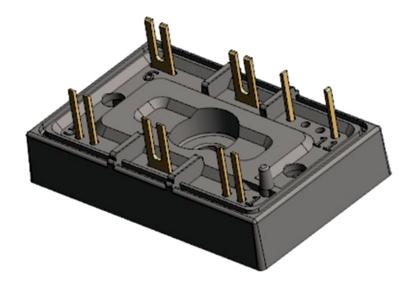
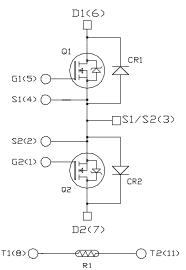
# MSCSM120DUM31CTBL1NG

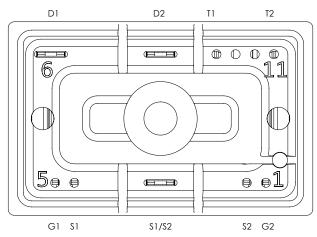
### **Dual Common Source SiC MOSFET Power Module**

### **Product Overview**

The MSCSM120DUM31CTBL1NG device is a 1200 V, 79 A dual common source silicon carbide (SiC) MOSFET power module.







All ratings at T<sub>J</sub> = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are the key features of MSCSM120DUM31CTBL1NG device:

- · SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High speed switching
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on V<sub>F</sub>
- Ultra low weight and profile
- Kelvin source for easy drive
- Si<sub>3</sub>N<sub>4</sub> substrate with thick copper for improved thermal performance
- Internal thermistor for temperature monitoring
- Extended temperature range

#### **Benefits**

The following are the benefits of MSCSM120DUM31CTBL1NG device:

- · High efficiency converter
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant
- Solderable terminals both for power and signal for easy PCB mounting
- Very integrated power conversion system

### **Application**

The following are the applications of MSCSM120DUM31CTBL1NG device:

- · High reliability power systems
- · AC switches

DS00004081A-page 2 **Datasheet** 

### 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120DUM31CTBL1NG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of MSCSM120DUM31CTBL1NG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V <sub>DSS</sub>	Drain-Source voltage		1200	V
I <sub>D</sub>	Continuous drain current	T <sub>H</sub> = 25 °C	79	Α
		T <sub>H</sub> = 80 °C	63	
I <sub>DM</sub>	Pulsed drain current		160	
V <sub>GS</sub>	Gate-Source voltage		-10/25	V
R <sub>DS(on)</sub>	Drain-Source ON resistance		31	mΩ
P <sub>D</sub>	Power dissipation	T <sub>H</sub> = 25 °C	310	W

The following table lists the electrical characteristics of MSCSM120DUM31CTBL1NG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 1200 V		_	10	100	μΑ
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20 V	T <sub>J</sub> = 25 °C	_	25	31	mΩ
	resistance	I <sub>D</sub> = 40 A	T <sub>J</sub> = 175 °C	_	40	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 1 \text{ mA}$		1.8	2.8	_	V
I <sub>GSS</sub>	Gate–Source leakage current	V <sub>GS</sub> = 20 V V <sub>DS</sub> = 0 V		_	_	150	nA

The following table lists the dynamic characteristics of MSCSM120DUM31CTBL1NG device.

**Table 1-3. Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V		_	3020	_	pF
Coss	Output capacitance	V <sub>DS</sub> = 1000 V		_	270	_	
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	25	_	
Qg	Total gate charge	V <sub>GS</sub> = -5 V/20 V		_	232	_	nC
Qgs	Gate-Source charge	V <sub>Bus</sub> = 800 V		_	41	_	
Qgd	Gate-Drain charge	I <sub>D</sub> = 40 A		_	50	_	
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5 V/20 V		_	30	_	ns
Tr	Rise time	V <sub>Bus</sub> = 600 V		_	30	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 50 A		_	50	_	
Tf	Fall time	R <sub>Gon</sub> = 8 Ω R <sub>Goff</sub> = 4.7 Ω			25	_	
Eon	Turn-on energy	V <sub>GS</sub> = -5 V/20 V	T <sub>J</sub> = 150 °C	_	0.99	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus}$ = 600 V $I_{D}$ = 50 A $R_{Gon}$ = 8 Ω $R_{Goff}$ = 4.7 Ω	TJ = 150 °C	_	0.66	_	
RGint	Internal gate resistance		_	0.88	_	Ω	
RthJH	Junction-to-heatsink there	mal resistance	λ = 3.4 W/mK	_	0.483	_	°C/W

The following table lists the body diode ratings and characteristics of MSCSM120DUM31CTBL1NG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V <sub>SD</sub>	Diode forward voltage	V <sub>GS</sub> = 0 V	_	4	_	V
		I <sub>SD</sub> = 40 A				
		V <sub>GS</sub> = -5 V	_	4.2	_	
		I <sub>SD</sub> = 40 A				
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 40 A	_	90	_	ns
Q <sub>rr</sub>	Reverse recovery charge	V <sub>GS</sub> = -5 V	_	550	_	nC
Irr	Reverse recovery current	V <sub>R</sub> = 800 V		13.5	_	Α
		di <sub>F</sub> /dt = 1000 A/μs				

#### 1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of MSCSM120DUM31CTBL1NG device.

Table 1-5. SiC Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditi	ons		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak repetitive reverse vo	oltage			<u> </u>	_	1200	V
I <sub>RM</sub>	Reverse leakage current	V <sub>R</sub> = 1200 V		T <sub>J</sub> = 25 °C	_	10	200	μΑ
				T <sub>J</sub> = 175 °C	_	150	_	
I <sub>F</sub>	DC forward current	T <sub>H</sub> = 100 °C		_	30	_	A	
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 30 A		T <sub>J</sub> = 25 °C	_	1.5	1.8	V
				T <sub>J</sub> = 175 °C	_	2.1	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 600 V			_	130	_	nC
С	Total capacitance	f = 1 MHz V <sub>R</sub> = 400 V			_	141	_	pF
		f = 1 MHz V <sub>R</sub> = 800 V		_	105	_		
R <sub>thJH</sub>	Junction-to-heatsink therr resistance	nal	$\lambda_{\text{paste}} = 3$	.4 W/mK	_	0.854	_	°C/W

### 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120DUM31CTBL1NG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			2500	_	_	V
$T_{J}$	Operating junction temperature re	ange		<b>–</b> 55	_	175	°C
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			<b>-</b> 55	_	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage case temperature			<b>–</b> 55	_	125	
T <sub>C</sub>	Operating case temperature			<b>-</b> 55	_	125	
Torque	Mounting torque	To heatsink	M4	1.5	_	2	N.m
Wt	Package weight			_	13.5	_	g

The following table lists the temperature sensor NTC of the MSCSM120DUM31CTBL1NG device.

Table 1-7. Temperature Sensor NTC

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_		_	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

### 1.4 Typical SiC MOSFET Performance Curve (Per SiC MOSFET)

This section shows the typical SiC MOSFET performance curves of the MSCSM120DUM31CTBL1NG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

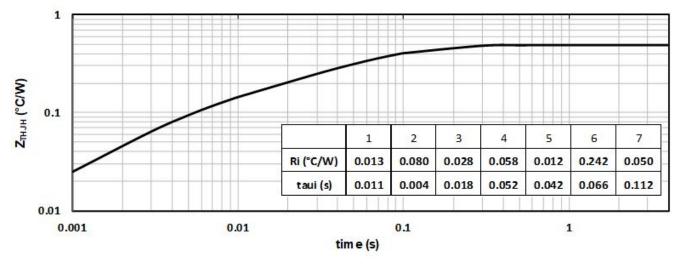


Figure 1-2. Output Characteristics,  $T_J = 25$  °C

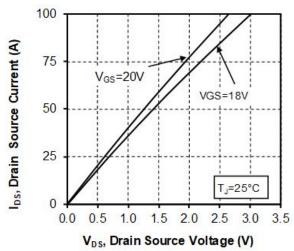


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C

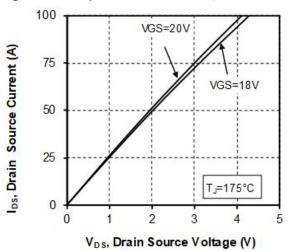


Figure 1-4. Normalized R<sub>DS(on)</sub> vs. Temperature

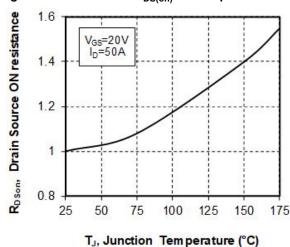


Figure 1-5. Transfer Characteristics

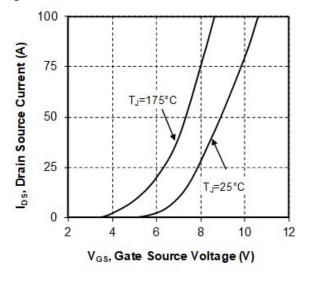


Figure 1-6. Switching Energy vs. Rg

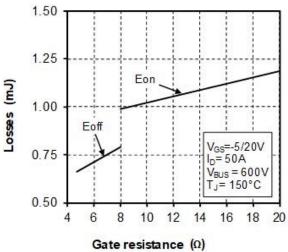


Figure 1-7. Switching Energy vs. Current

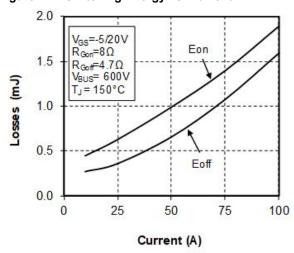


Figure 1-8. Capacitance vs. Drain Source Voltage

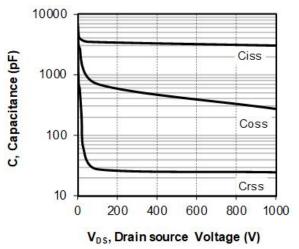


Figure 1-9. Gate Charge vs. Gate Source Voltage

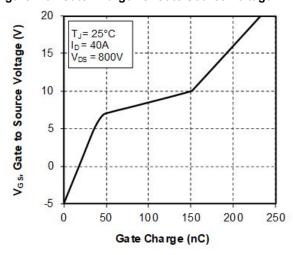


Figure 1-10. Body Diode Characteristics,  $T_J = 25$  °C

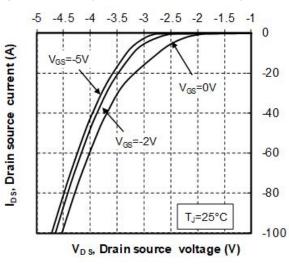


Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 25 °C

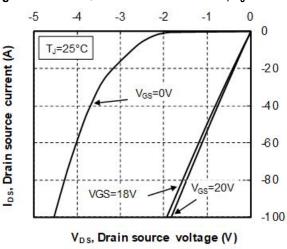
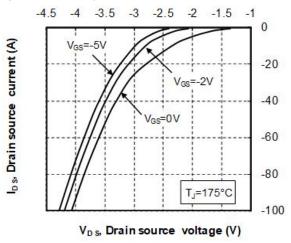


Figure 1-12. Body Diode Characteristics, T<sub>J</sub> = 175 °C Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 175 °C



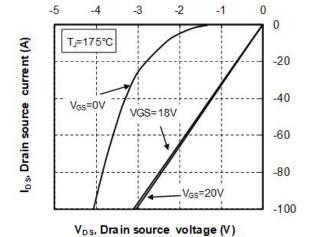
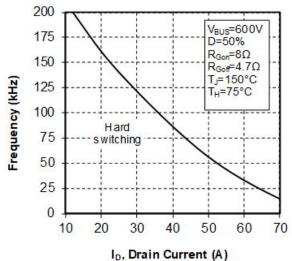


Figure 1-14. Operating Frequency vs Drain Current



### 1.5 Typical SiC Diode Performance Curves (Per SiC Diode)

This section shows the typical SiC diode performance curves of the MSCSM120DUM31CTBL1NG device.

Figure 1-15. Junction-to-Heatsink Thermal Impedance

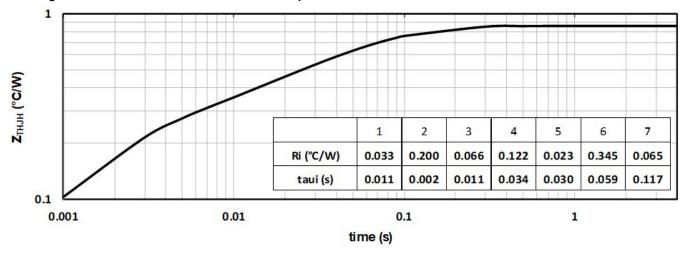


Figure 1-16. Forward Characteristics

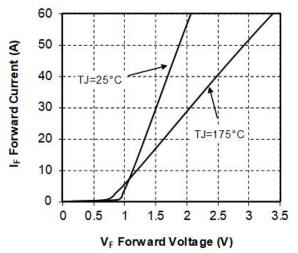
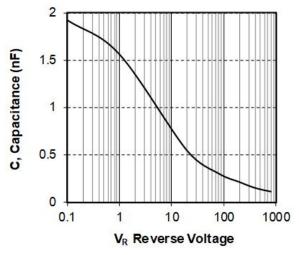


Figure 1-17. Capacitance vs. Reverse Voltage



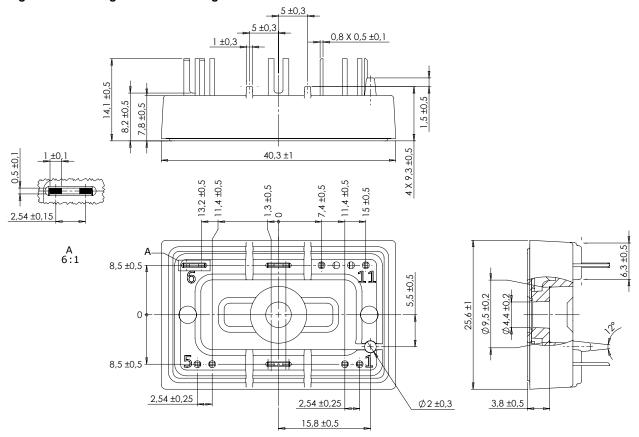
### 2. Package Specifications

The following section shows the package specification of the MSCSM120DUM31CTBL1NG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120DUM31CTBL1NG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



## MSCSM120DUM31CTBL1NG

**Revision History** 

# 3. Revision History

Revision	Date	Description
Α	07/2021	Initial Revision

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